

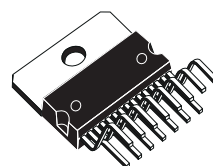
11W+11W AMPLIFIER

- 11+11W OUTPUT POWER
 $R_L = 8\Omega$ @THD = 10% $V_{CC} = 28V$
- ST-BY AND MUTE FUNCTIONS
- LOW TURN-ON TURN-OFF POP NOISE
- NO BOUCHEROT CELL
- NO ST-BY RC INPUT NETWORK
- SINGLE SUPPLY RANGING UP TO 35V
- SHORT CIRCUIT PROTECTION
- THERMAL OVERLOAD PROTECTION
- INTERNALLY FIXED GAIN
- SOFT CLIPPING
- MULTIWATT 15 PACKAGE

DESCRIPTION

The TDA7495S is a stereo 11+11W class AB power amplifier assembled in the @ Multiwatt 15 package, specially designed for high quality sound, TV applications.

MULTIPOWER BI50II TECHNOLOGY

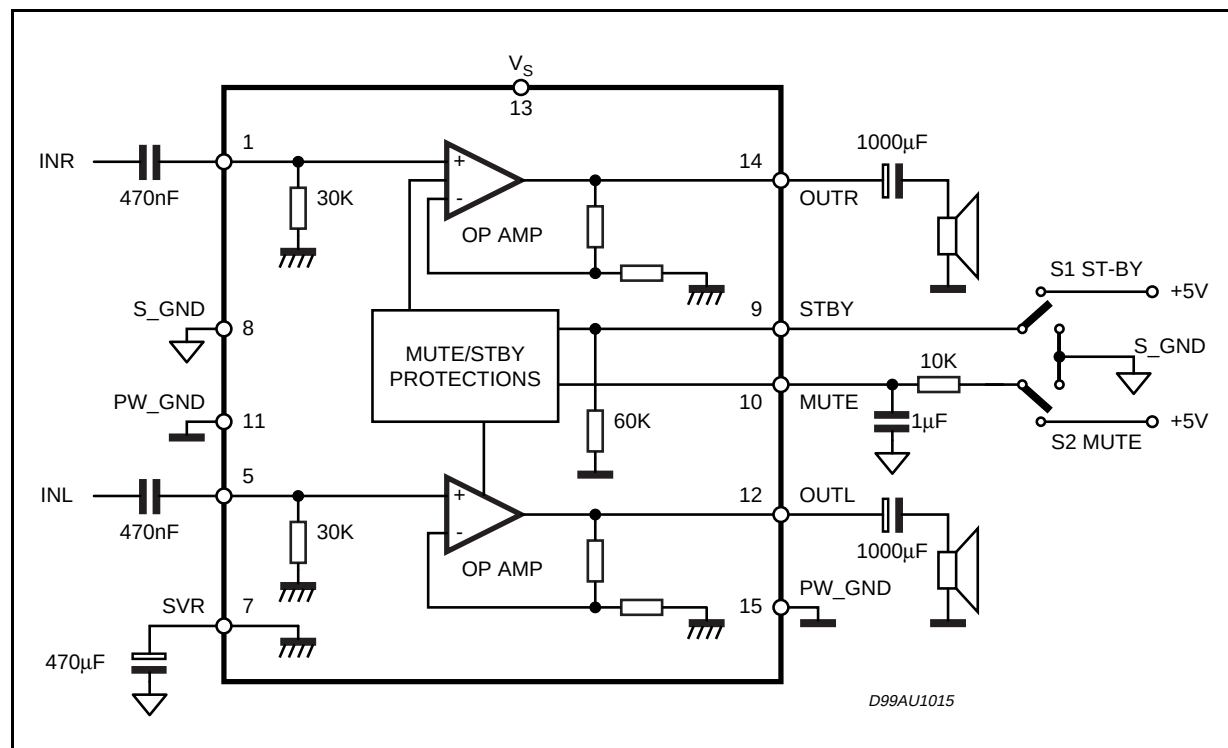


Multiwatt15

ORDERING NUMBER: TDA7495S

Features of the TDA7495S include linearStand-by and mute functions.

BLOCK AND APPLICATION DIAGRAM

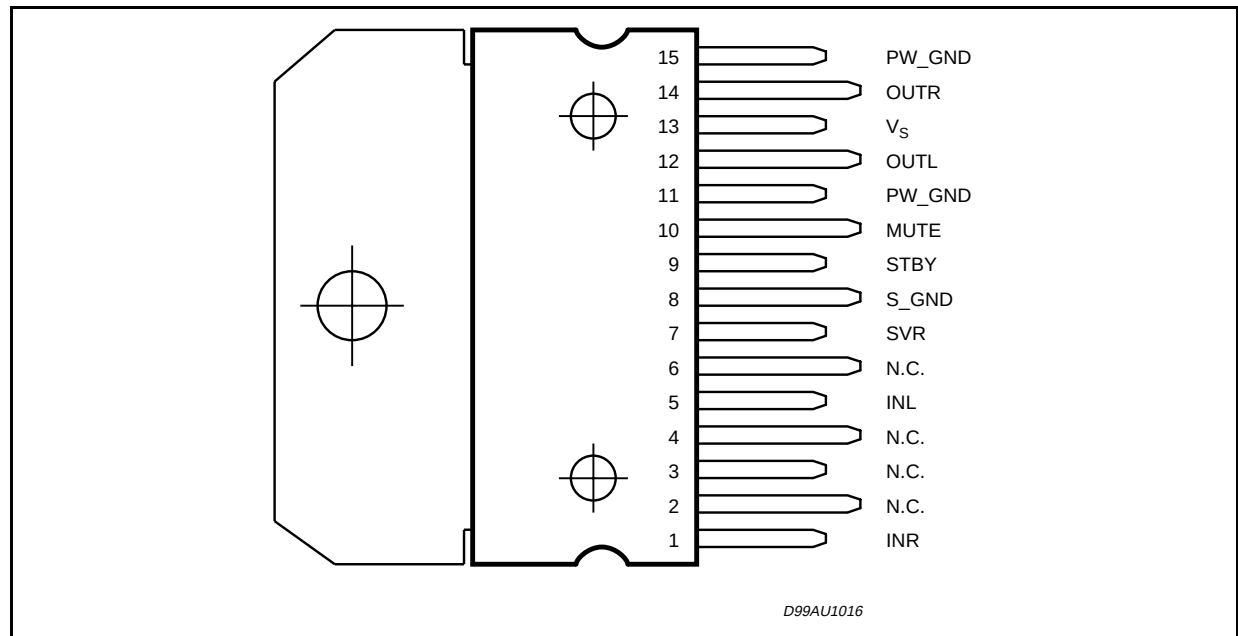


ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_S	DC Supply Voltage	40	V
V_{IN}	Maximum Input Voltage	8	V _{pp}
P_{tot}	Total Power Dissipation ($T_{amb} = 70^{\circ}\text{C}$)	20	W
T_{amb}	Ambient Operating Temperature (1)	-20 to 85	$^{\circ}\text{C}$
T_{stg}, T_j	Storage and Junction Temperature	-40 to 150	$^{\circ}\text{C}$

(1) Operation between -20 to 85 $^{\circ}\text{C}$ guaranteed by correlation with 0 to 70 $^{\circ}\text{C}$.

PIN CONNECTION (Top view)



THERMAL DATA

Symbol	Parameter	Value	Unit
$R_{th\ j-case}$	Thermal Resistance Junction-case	Typ. = 2 Max. = 2.8	$^{\circ}\text{C}/\text{W}$
$R_{th\ j-amb}$	Thermal Resistance Junction-ambient	max 35	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS (Refer to the test circuit $V_S = 20\text{V}$; $R_L = 8\Omega$, $R_g = 50\Omega$, $T_{amb} = 25^{\circ}\text{C}$).

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V_S	Supply Voltage Range		11		35	V
I_q	Total Quiescent Current			70	100	mA
DCVos	Output DC Offset Referred to SVR Potential	No Input Signal	-750		750	mV
V_O	Quiescent Output Voltage	$V_S = 20\text{V}$	8.5	10	11.5	V
P_O	Output Power	THD = 10%; $R_L = 8\Omega$; $V_S = 28\text{V}$	9.5	11		W
		THD = 1%; $R_L = 8\Omega$; $V_S = 28\text{V}$	7.5	8.8		W
		THD = 10%; $R_L = 4\Omega$; $V_S = 20\text{V}$	7	8.7		W
		THD = 1%; $R_L = 4\Omega$; $V_S = 20\text{V}$	5	6.8		W
		THD = 10%; $R_L = 8\Omega$; $V_S = 18\text{V}$	3.5	4		W
		THD = 1%; $R_L = 8\Omega$; $V_S = 18\text{V}$	2.2	3.2		W

ELECTRICAL CHARACTERISTICS (continued)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
THD	Total Harmonic Distortion	$G_V = 30\text{dB}$; $P_O = 1\text{W}$; $f = 1\text{kHz}$;			0.4	%
I_{peak}	Output Peak Current	(internally limited)	1.7	2.4		A
V_{in}	Input Signal				2.8	V _{rms}
BW				0.6		MHz
e_N	Total Output Noise	$f = 20\text{Hz to } 22\text{kHz}$ Play		60	150	μV
		$f = 20\text{Hz to } 22\text{kHz}$ Mute		60	150	μV
SR	Slew Rate		5	8		V/ μs
R_i	Input Resistance		22.5	30		$\text{k}\Omega$
SVR	Supply Voltage Rejection	$f = 1\text{kHz}$; max volume $C_{\text{SVR}} = 470\mu\text{F}$; $V_{\text{RIP}} = 1\text{V}_{\text{rms}}$	35	39		dB
T_M	Thermal Muting			150		$^{\circ}\text{C}$
T_S	Thermal Shut-down			160		$^{\circ}\text{C}$
MUTE STAND-BY & INPUT SELECTION FUNCTIONS						
$V_{\text{ST-BY}}$	Stand-by threshold		2.3	2.5	2.7	V
V_{MUTE}	Mute Threshold		2.3	2.5	2.7	V
$I_{\text{qST-BY}}$	Quiescent Current @ Stand-by			0.6	1	mA
A_{MUTE}	Mute Attenuation		50	65		dB
I_{stbyBIAS}	Stand-by bias current	Stand by on $V_{\text{ST-BY}} = 5\text{V}$ $V_{\text{MUTE}} = 5\text{V}$		80		μA
		Play or Mute	-20	-5		μA
I_{muteBIAS}	Mute bias current	Mute		1	5	μA
		Play		0.2	2	μA

Figure 1a: Application Circuit.

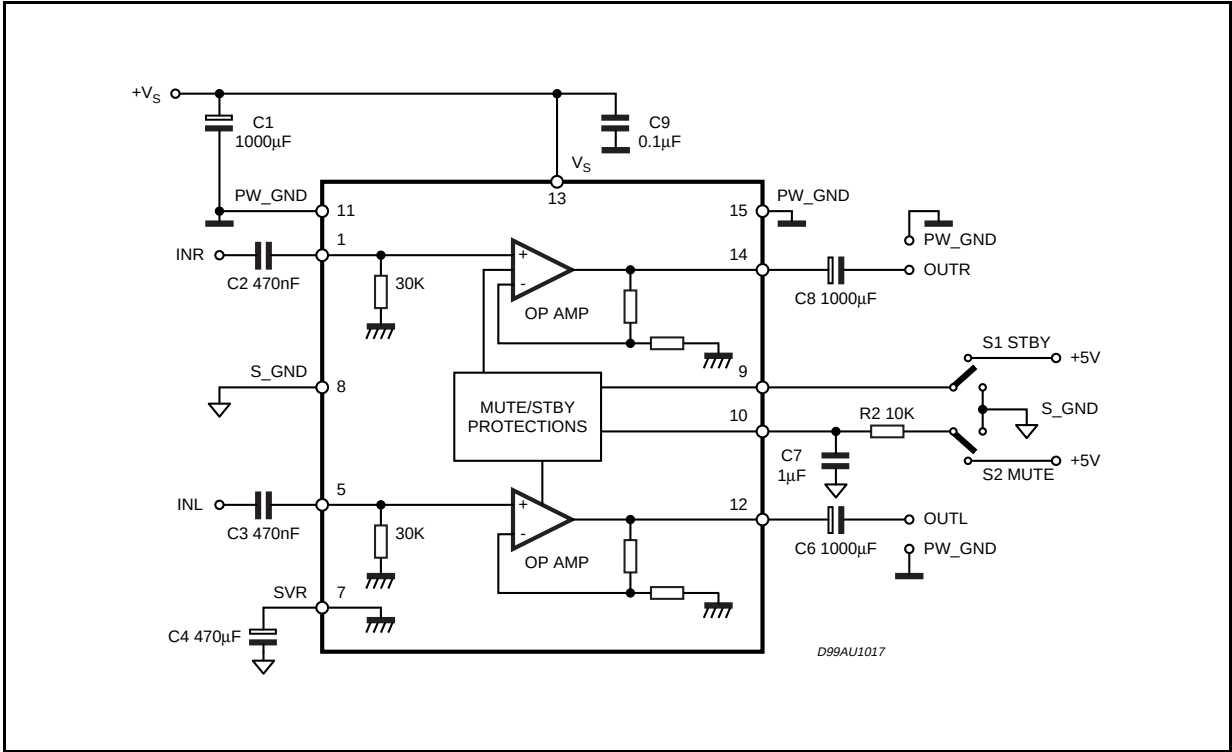
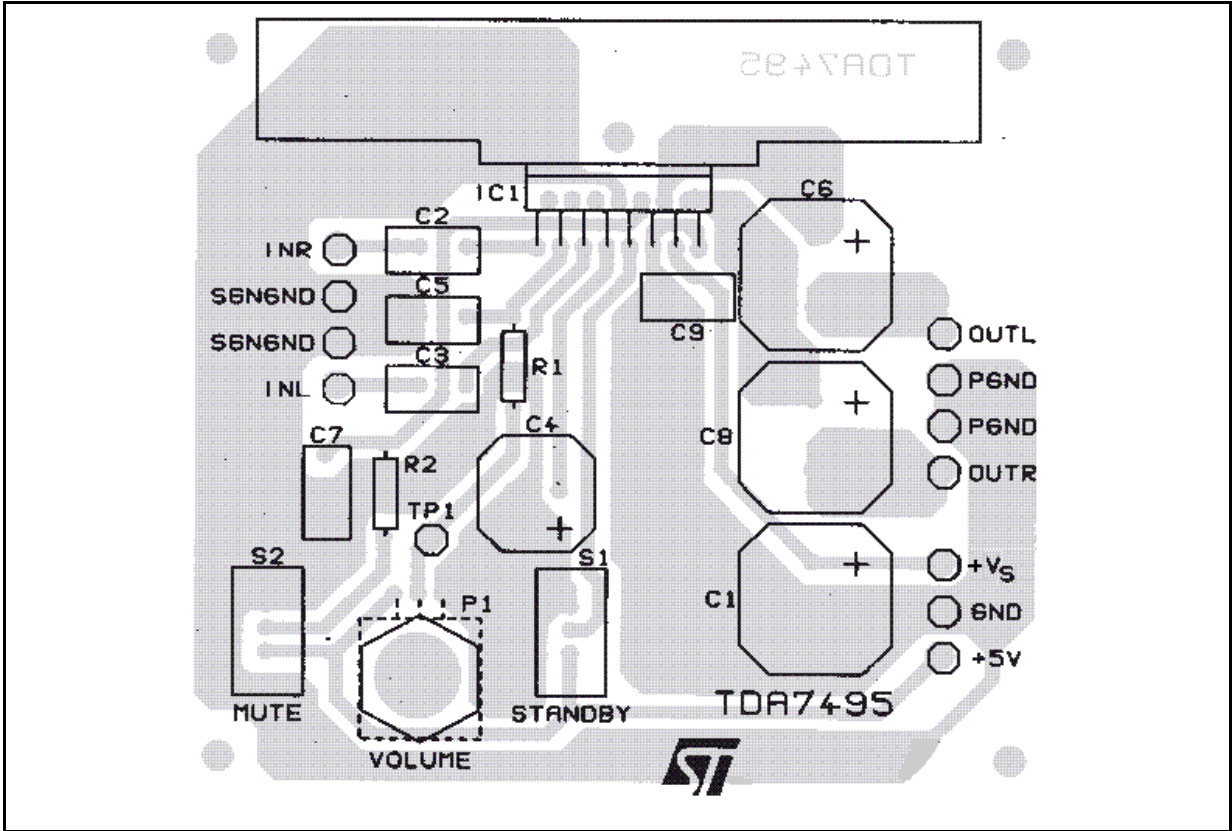


Figure 1b: P.C.B. and Component Layout.



APPLICATION SUGGESTIONS

The recommended values of the external components are those shown on the application circuit of figure 1a. Different values can be used, the following table can help the designer.

COMPONENT	SUGGESTION VALUE	PURPOSE	LARGER THAN SUGGESTION	SMALLER THAN SUGGESTION
R2	10K	Mute time constant	Larger mute on/off time	Smaller mute on/off time
C1	1000 μ F	Supply voltage bypass		Danger of oscillation
C2	470nF	Input DC decoupling	Lower low frequency cutoff	Higher low frequency cutoff
C3	470nF	Input DC decoupling	Lower low frequency cutoff	Higher low frequency cutoff
C4	470 μ F	Ripple rejection	Better SVR	Worse SVR
C6	1000 μ F	Output DC decoupling	Lower low frequency cutoff	Higher low frequency cutoff
C7	1 μ F	Mute time constant	Larger mute on/off time	Smaller mute on/off time
C8	1000 μ F	Output DC decoupling	Lower low frequency cutoff	Higher low frequency cutoff
C9	100nF	Supply voltage bypass		Danger of oscillation

TYPICAL CHARACTERISTICS:

Refer to the application circuit of fig.1A $T_{amb} = 25^{\circ}\text{C}$; $V_S = 20\text{V}$; $R_L = 8\Omega$; $F = 1\text{KHz}$; $R_s = 50\Omega$; unless otherwise specified.

Figure 2: Output Power vs Supply Voltage

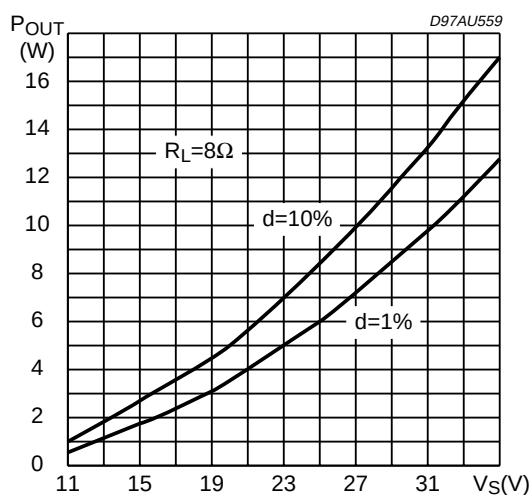


Figure 3: Distortion vs Output Power

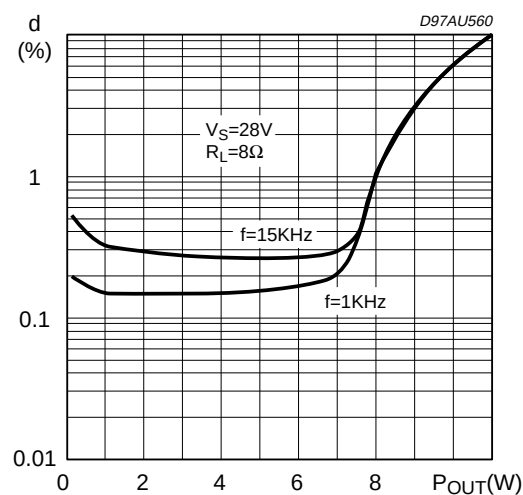


Figure 4: Output Power vs Supply Voltage

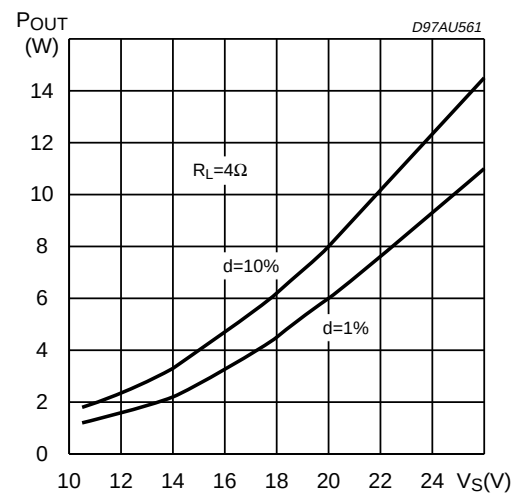


Figure 6: Stand-by Attenuation vs Vpin #9

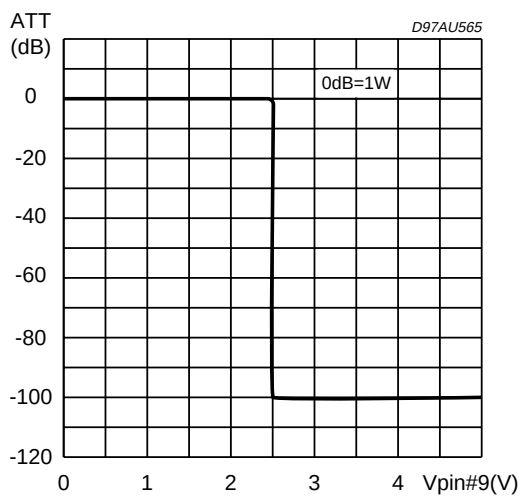


Figure 8: Power dissipation vs Output Power

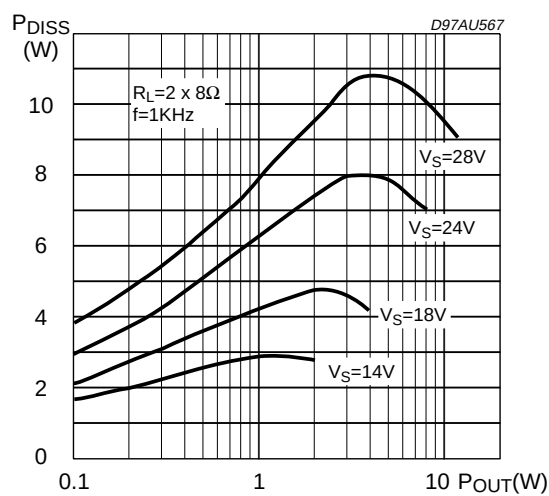


Figure 5: Distortion vs Output Power

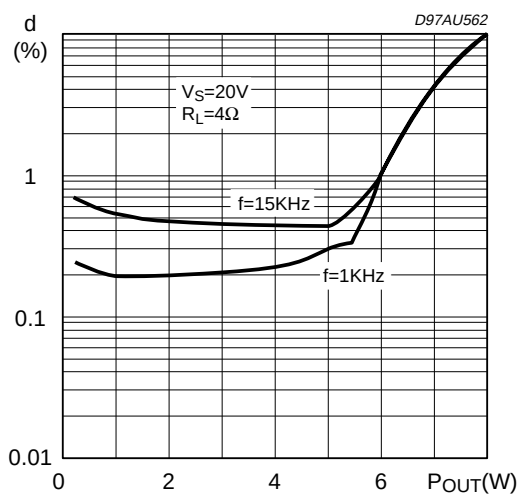


Figure 7: Mute Attenuation vs V pin #10

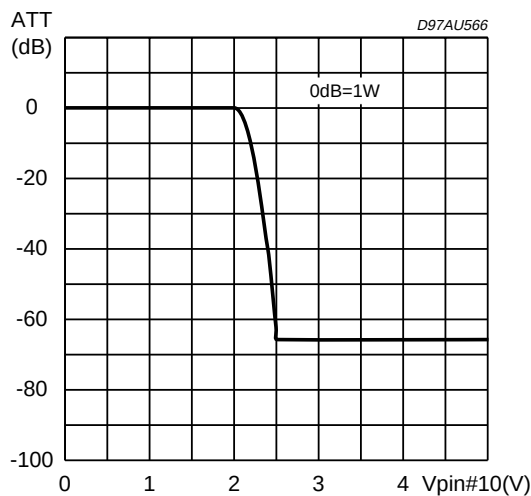
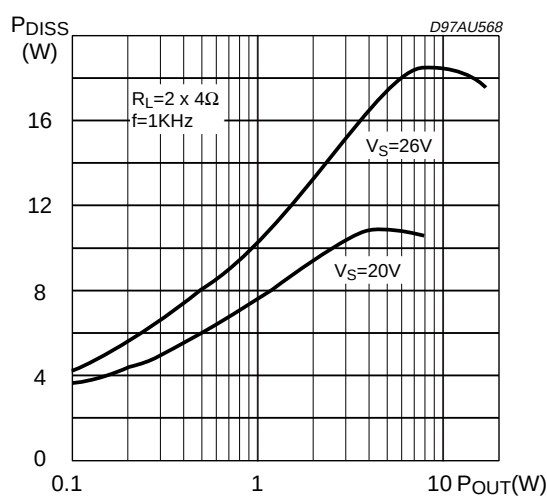


Figure 9: Power Dissipation vs Output Power

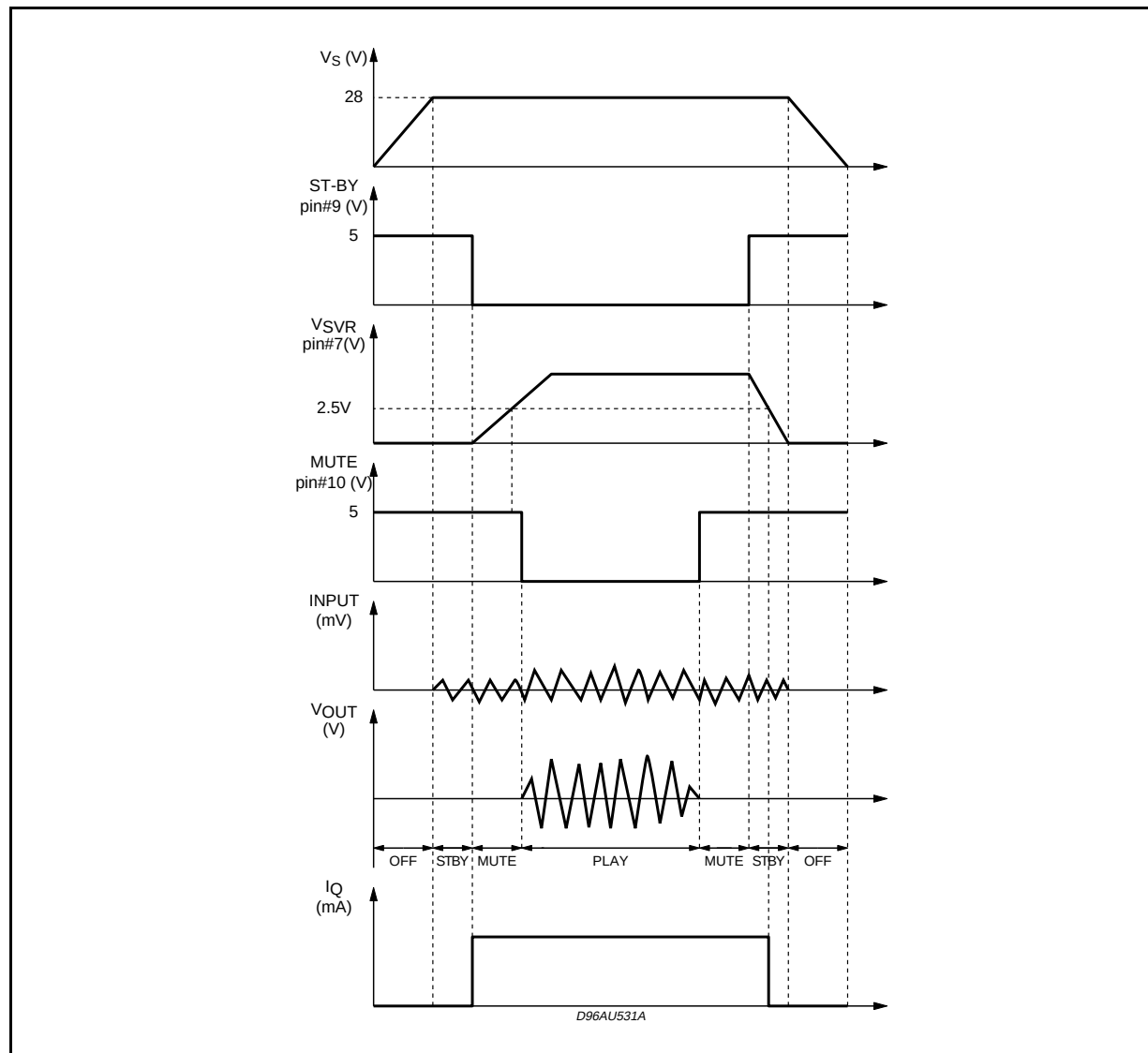


MUTE STAND-BY TRUTH TABLE

MUTE	ST-BY	OPERATING CONDITION
H	H	STANDBY
L	H	STANDBY
H	L	MUTE
L	L	PLAY

Turn ON/OFF Sequences (for optimizing the POP performances)

A) USING MUTE AND STAND-BY FUNCTIONS



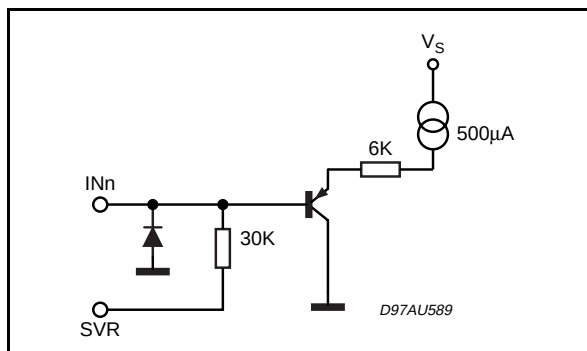
B) USING ONLY THE MUTE FUNCTION

To simplify the application, the stand-by pin can be connected directly to Ground.

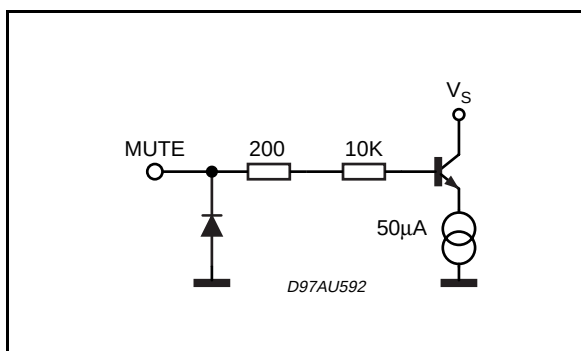
During the ON/OFF transitions we recommend to respect the following conditions:

- At the turn-on the transition mute to play must be made when the SVR pin is higher than 2.5V
- At the turn-off the TDA7495S must be brought to mute from the play condition when the SVR pin is higher than 2.5V.

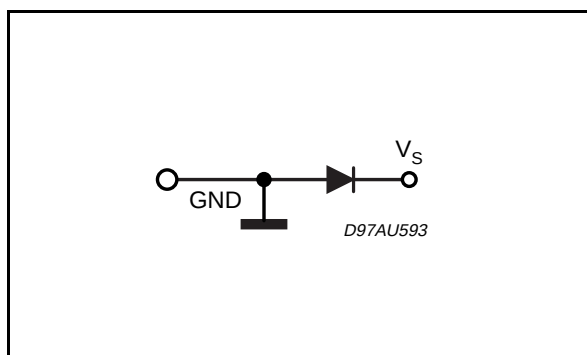
PINS: INL, INR



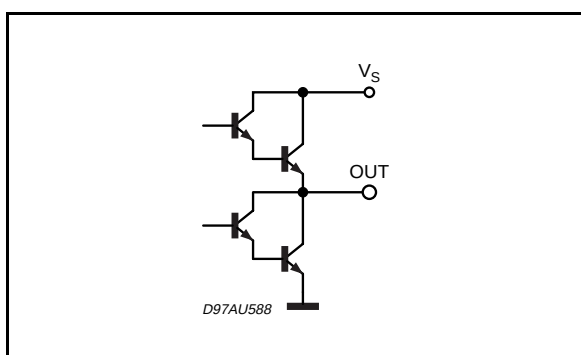
PIN: MUTE



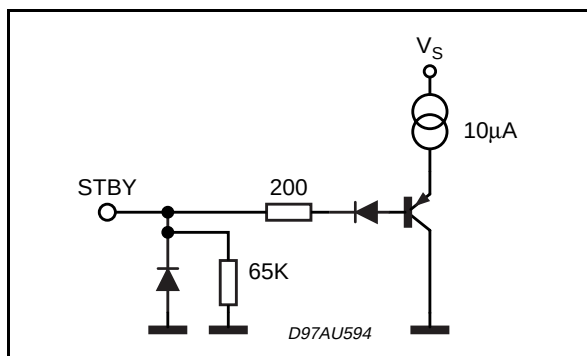
PINS: PW-GND, S-GND



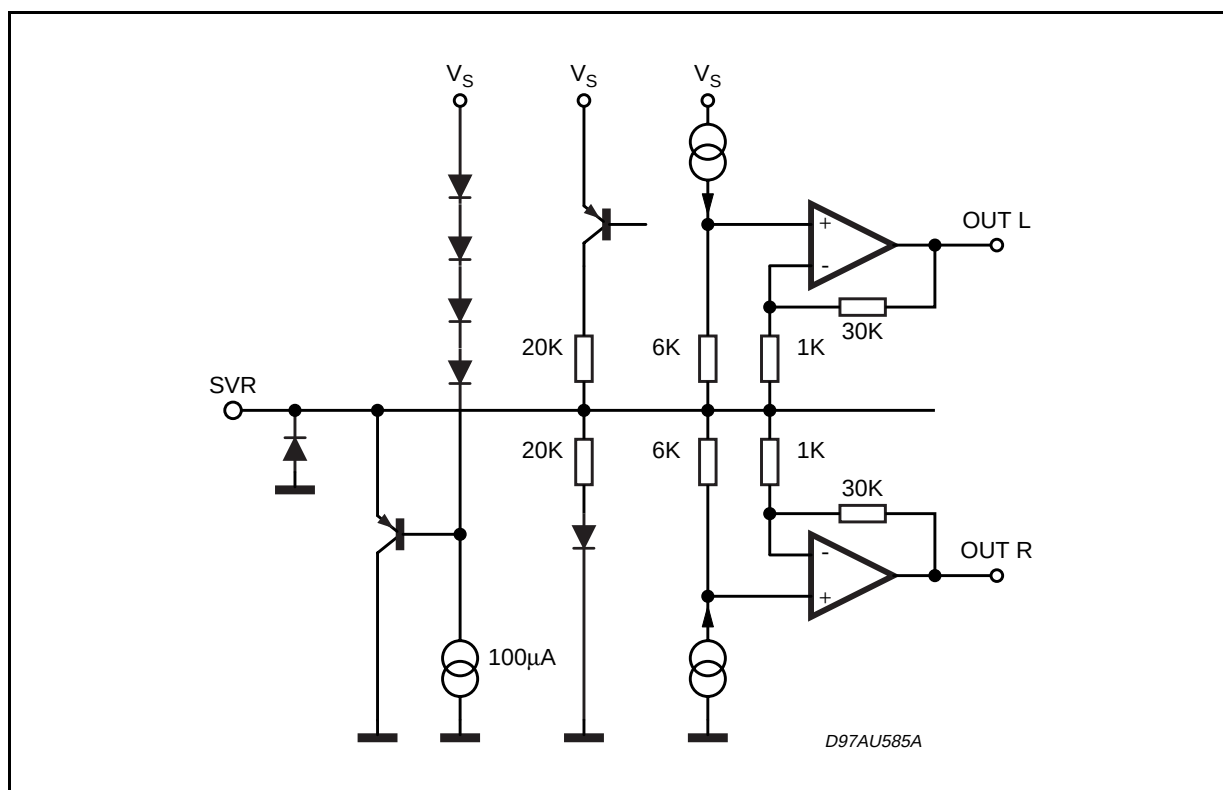
PINS: OUT R, OUT L



PIN: STBY

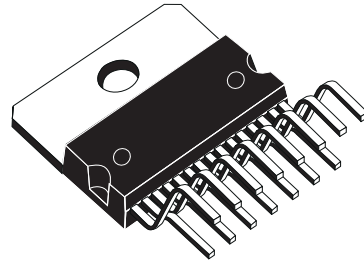


PIN: SVR

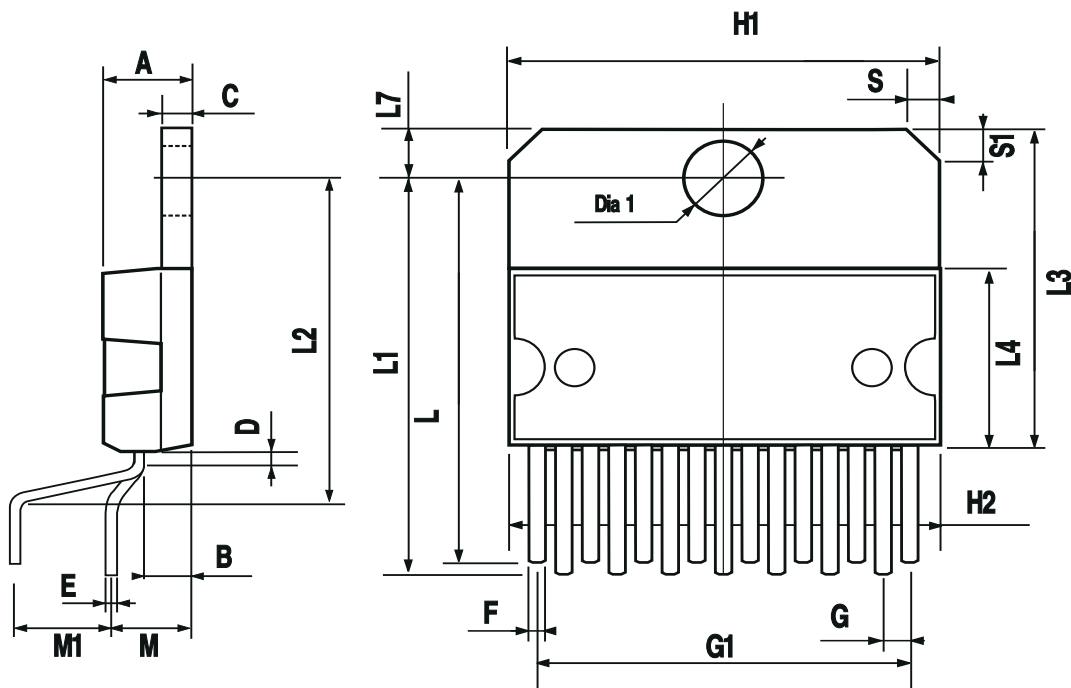


DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			5			0.197
B			2.65			0.104
C			1.6			0.063
D		1			0.039	
E	0.49		0.55	0.019		0.022
F	0.66		0.75	0.026		0.030
G	1.02	1.27	1.52	0.040	0.050	0.060
G1	17.53	17.78	18.03	0.690	0.700	0.710
H1	19.6			0.772		
H2			20.2			0.795
L	21.9	22.2	22.5	0.862	0.874	0.886
L1	21.7	22.1	22.5	0.854	0.870	0.886
L2	17.65		18.1	0.695		0.713
L3	17.25	17.5	17.75	0.679	0.689	0.699
L4	10.3	10.7	10.9	0.406	0.421	0.429
L7	2.65		2.9	0.104		0.114
M	4.25	4.55	4.85	0.167	0.179	0.191
M1	4.63	5.08	5.53	0.182	0.200	0.218
S	1.9		2.6	0.075		0.102
S1	1.9		2.6	0.075		0.102
Dia1	3.65		3.85	0.144		0.152

OUTLINE AND MECHANICAL DATA



Multiwatt15 V



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